

REPLACEMENT CLAIMS

13. (twice amended) A method of fabricating a semiconductor device, the method comprising:

depositing a dielectric film over an active region of a semiconductor substrate to form part of a gate of a transistor; and

subjecting the dielectric film to a wet oxidation with steam provided by heating a mixture of hydrogen and oxygen gases in a rapid thermal process chamber at a temperature greater than about 450 °C.

14. (amended) The method of claim 13 wherein the wet oxidation process is performed at a temperature in the range of about 750 °C to about 950 °C and for a duration of about 20 seconds to about 60 seconds.

41. (amended) A method of fabricating a semiconductor device, the method comprising:

depositing a dielectric film with a thickness greater than about 40 Angstroms over a semiconductor substrate; and

subjecting the dielectric film to a wet oxidation in a rapid thermal process chamber at a temperature greater than about 450 °C.